1-of-8 Decoder/ Demultiplexer with LSTTL Compatible Inputs

High-Performance Silicon-Gate CMOS

The MC74HCT138A is identical in pinout to the LS138. The HCT138A may be used as a level converter for interfacing TTL or NMOS outputs to High Speed CMOS inputs.

The HCT138A decodes a three-bit Address to one-of-eight active-lot outputs. This device features three Chip Select inputs, two active-low and one active-high to facilitate the demultiplexing, cascading, and chip-selecting functions. The demultiplexing function is accomplished by using the Address inputs to select the desired device output; one of the Chip Selects is used as a data input while the other Chip Selects are held in their active states.

Features

- Output Drive Capability: 10 LSTTL Loads
- TTL/NMOS Compatible Input Levels
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 4.5 to 5.5 V
- Low Input Current: 1.0 μA
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- Chip Complexity: 122 FETs or 30.5 Equivalent Gates
- Pb-Free Packages are Available*



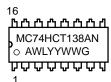
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MARKING DIAGRAMS

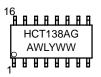


PDIP-16 N SUFFIX CASE 648





SOIC-16 D SUFFIX CASE 751B





TSSOP-16 DT SUFFIX CASE 948F



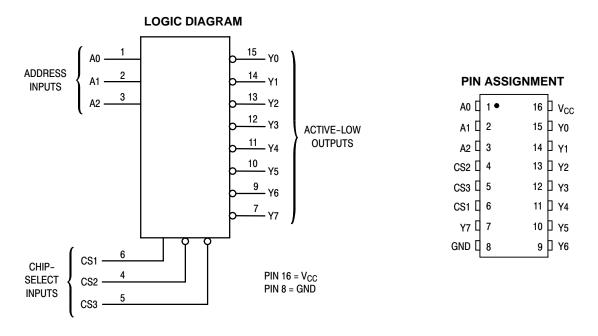
A = Assembly Location

WL, L = Wafer Lot
 Y, YY = Year
 W, WW = Work Week
 G = Pb-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



Design Criteria	Value	Units
Internal Gate Count*	30.5	ea.
Internal Gate Propagation Delay	1.5	ns
Internal Gate Power Dissipation	5.0	μW
Speed Power Product	.0075	рЈ

^{*}Equivalent to a two-input NAND gate.

FUNCTION TABLE

	Inputs						Ou	tput	s				
CS1	CS2	CS3	A2	A 1	Α0	Y0	Y1	Y2	Y3	Y4	Y5	Y6	Y7
Х	Х	Н	Х	Χ	Χ	Н	Н	Н	Н	Н	Н	Н	Н
X	Н	Χ	Х	Χ	Χ	Н	Н	Н	Н	Н	Н	Н	Н
L	Χ	Χ	Χ	Χ	Χ	Н	Н	Н	Н	Н	Н	Н	Н
Н	L	L	L	L	L	L	Н	Н	Н	Н	Н	Н	Н
Н	L	L	L	L	Н	Н	L	Н	Н	Н	Н	Н	Н
Н	L	L	L	Н	L	Н	Н	L	Н	Н	Н	Н	Н
Н	L	L	L	Н	Η	Н	Н	Н	L	Н	Н	Н	Н
Н	L	L	Н	L	L	Н	Н	Н	Н	L	Н	Н	Н
Н	L	L	Н	L	Н	Н	Н	Н	Н	Н	L	Н	Н
Н	L	L	Н	Н	L	Н	Н	Н	Н	Н	Н	L	Н
Н	L	L	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	L

H = high level (steady state)

L = low level (steady state)

X = don't care

ORDERING INFORMATION

Device	Package	Shipping [†]
MC74HCT138AN	PDIP-16	500 Units / Box
MC74HCT138ANG	PDIP-16 500 Units / Box (Pb-Free)	
MC74HCT138AD	SOIC-16	48 Units / Rail
MC74HCT138ADG	SOIC-16 (Pb-Free)	48 Units / Rail
MC74HCT138ADR2	SOIC-16	2500 Units / Tape & Reel
MC74HCT138ADR2G	SOIC-16 (Pb-Free)	2500 Units / Tape & Reel
MC74HCT138ADTR2	TSSOP-16*	2500 Units / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*This package is inherently Pb–Free.

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V
V _{in}	DC Input Voltage (Referenced to GND)	- 0.5 to V _{CC} + 0.5	V
V _{out}	DC Output Voltage (Referenced to GND)	- 0.5 to V _{CC} + 0.5	V
I _{in}	DC Input Current, per Pin	± 20	mA
l _{out}	DC Output Current, per Pin	± 25	mA
I _{CC}	DC Supply Current, V _{CC} and GND Pins	± 50	mA
P _D	Power Dissipation in Still Air Plastic DIP† SOIC Package† TSSOP Package†	750 500 450	mW
T _{stg}	Storage Temperature	- 65 to + 150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP, TSSOP or SOIC Package)	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC} .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

†Derating — Plastic DIP: – 10 mW/°C from 65° to 125°C

SOIC Package: - 7 mW/°C from 65° to 125°C

TSSOP Package: - 6.1 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	4.5	5.5	V
V _{in} , V _{out}	DC Input Voltage, Output Voltage (Referenced to GND)	0	V _{CC}	V
T _A	Operating Temperature, All Package Types	- 55	+ 125	°C
t _r , t _f	Input Rise and Fall Time (Figure 1)	0	500	ns

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Gu	aranteed Li	mit	
Symbol	Parameter	Test Conditions	V _{CC}	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
V _{IH}	Minimum High-Level Input Voltage	$V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out} \le 20 \mu\text{A}$	4.5 5.5	2.0 2.0	2.0 2.0	2.0 2.0	V
V _{IL}	Maximum Low–Level Input Voltage	$V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out} \le 20 \mu\text{A}$	4.5 5.5	0.8 0.8	0.8 0.8	0.8 0.8	V
V _{OH}	Minimum High-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 20 \ \mu\text{A}$	4.5 5.5	4.4 5.4	4.4 5.4	4.4 5.4	V
		$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 4.0 \mu A$	4.5	3.98	3.84	3.7	
V _{OL}	Maximum Low–Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 20 \ \mu\text{A}$	4.5 5.5	0.1 0.1	0.1 0.1	0.1 0.1	V
		$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 4.0 \text{ mA}$	4.5	0.26	0.33	0.4	
I _{in}	Maximum Input Leakage Current	$V_{in} = V_{CC}$ or GND	6.0	± 0.1	± 1.0	± 1.0	μΑ
I _{CC}	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC}$ or GND $I_{out} = 0 \mu A$	5.5	4.0	40	160	μΑ
	Additional Quiescent Supply	V _{in} = 2.4 V, Any One Input V _{in} = V _{CC} or GND, Other Inputs		≥ - 55°C		125°C	
ΔI_{CC}	Current	$I_{out} = 0 \mu A$	5.5	2.9	2	.4	mA

NOTE:Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

AC ELECTRICAL CHARACTERISTICS (V_{CC} = $5.0 \text{ V} \pm 10\%$, C_L = 50 pF, Input t_r = t_f = 6.0 ns)

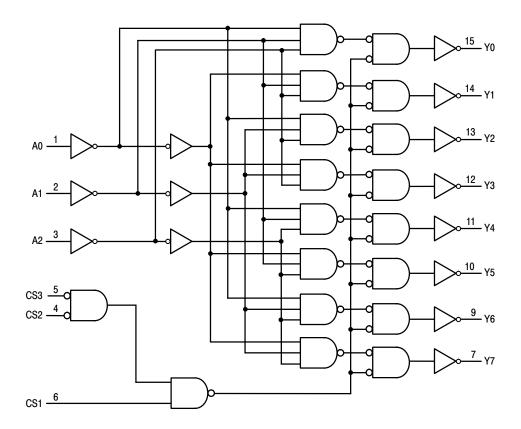
			Guaranteed Limit			
Symbol	Parameter	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit	
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Input A to Output Y (Figures 1 and 4)	30	38	45	ns	
t _{PLH} , t _{PHL}	Maximum Propagation Delay, CS1 to Output Y (Figures 2 and 4)	27	34	41	ns	
t _{PLH} , t _{PHL}	(=) (-)		38	45	ns	
t _{TLH} , t _{THL}	Maximum Output Transition Time, Any Output (Figures 2 and 4)	15	19	22	ns	
t _r , t _f	Maximum Input Rise and Fall Time	500	500	500	ns	
C _{in}	Maximum Input Capacitance	10	10	10	pF	

NOTE: For propagation delays with loads other than 50 pF, and information on typical parametric values, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

		Typical @ 25°C, V _{CC} = 5.0 V		Ī
C_{PD}	Power Dissipation Capacitance (Per Enabled Output)*	51	pF	

^{*} Used to determine the no–load dynamic power consumption: $P_D = C_{PD} \ V_{CC}^2 f + I_{CC} \ V_{CC}$. For load considerations, see Chapter 2 of the ON Semiconductor High–Speed CMOS Data Book (DL129/D).

EXPANDED LOGIC DIAGRAM



SWITCHING WAVEFORMS

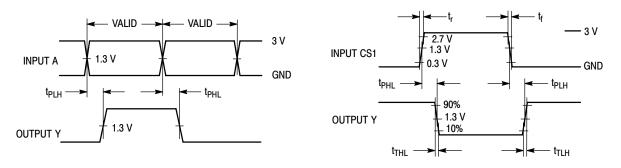


Figure 1.

Figure 2.

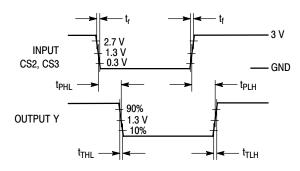
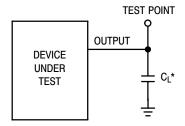


Figure 3.

TEST CIRCUIT

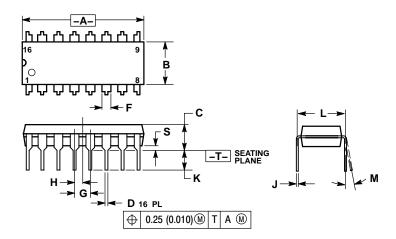


*Includes all probe and jig capacitance

Figure 4.

PACKAGE DIMENSIONS

PDIP-16 **N SUFFIX** CASE 648-08 **ISSUE T**

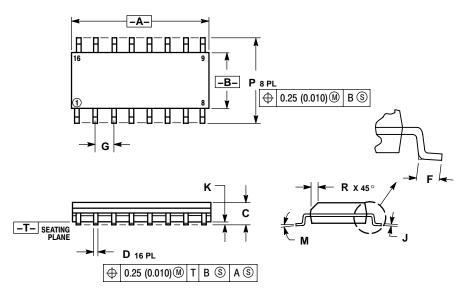


NOTES:

- DIMENSIONING AND TOLERANCING PER
- DIMENSIONING AND TOLERANCING F ANSI 714.5M, 1982.
 CONTROLLING DIMENSION: INCH.
 DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
 DIMENSION B DOES NOT INCLUDE MOLD FLASH.
- 5. ROUNDED CORNERS OPTIONAL.

	INC	HES	MILLIN	IETERS	
DIM	MIN	MAX	MIN	MAX	
Α	0.740	0.770	18.80	19.55	
В	0.250	0.270	6.35	6.85	
С	0.145	0.175	3.69	4.44	
D	0.015	0.021	0.39	0.53	
F	0.040	0.70	1.02	1.77	
G	0.100	BSC	2.54 BSC		
Н	0.050	BSC	1.27	BSC	
J	0.008	0.015	0.21	0.38	
K	0.110	0.130	2.80	3.30	
L	0.295	0.305	7.50	7.74	
M	0°	10 °	0°	10 °	
S	0.020	0.040	0.51	1.01	

SOIC-16 **D SUFFIX** CASE 751B-05 **ISSUE J**



- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.

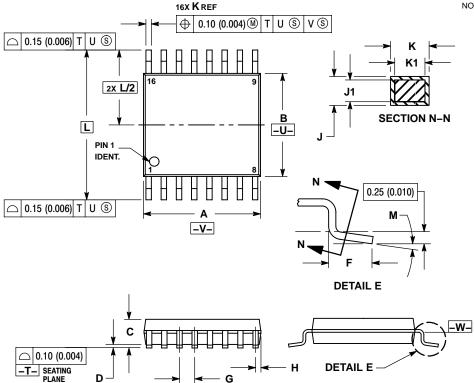
 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIGN.

- MAXIMUM MOLD PHOLICISION 0.15 (0.006)
 PER SIDE.
 DIMENSION D DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE DAMBAR
 PROTRUSION SHALL BE 0.127 (0.005) TOTAL
 IN EXCESS OF THE D DIMENSION AT
 MAXIMUM MATERIAL CONDITION.

	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	9.80	10.00	0.386	0.393	
В	3.80	4.00	0.150	0.157	
С	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27	BSC	0.050 BSC		
J	0.19	0.25	0.008	0.009	
K	0.10	0.25	0.004	0.009	
M	0°	7°	0°	7°	
P	5.80	6.20	0.229	0.244	
R	0.25	0.50	0.010	0.019	

PACKAGE DIMENSIONS

TSSOP-16 **DT SUFFIX** CASE 948F-01 **ISSUE A**



- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
 6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE —W—.

	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	4.90	5.10	0.193	0.200	
В	4.30	4.50	0.169	0.177	
C		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026 BSC		
Н	0.18	0.28	0.007	0.011	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40	BSC	0.252	BSC	
М	0 °	8 °	0 °	8 °	

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